

MMBTH10

VHF/UHF NPN SILICON TRANSISTOR

VOLTAGE 25 Volts **POWER** 225 mW

SOT-23 Unit : inch(mm)

MECHANICAL

Case : SOT-23, Plastic

Terminals : Solderable per MIL-STD-750, Method 2026

Approx weight :

MAXIMUM RATINGS

RATING	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	V _{CEO}	25	V _{dc}
Collector-Base Voltage	V _{CBO}	30	V _{dc}
Emitter-Base Voltage	V _{EB0}	3.0	V _{dc}

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNITS
Total Device Dissipation FR-5 Board (Note 1) T _A =25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient (Note 1)	R _{θJA}	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A =25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient (Note 2)	R _{θJA}	417	°C/W
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Note 1. FR-5 = 1.0 x 0.75 x 0.062 in

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina